

**IN THE CLAIMS**

Please amend claims 4, 9, 14, 19, 21 and 26 as follows:

Claims 1-3. (Canceled)

1           4. (Currently Amended) A thin film transistor, comprising a source electrode, a drain  
2 electrode, a gate electrode, and a semiconductor layer;

3           wherein one of the source electrode, the drain electrode, and the gate electrode  
4 comprises ~~an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer~~  
5 ~~interposed between the titanium and the aluminum-based layers~~ an orderly stacked structure  
6 of a titanium layer, a diffusion prevention layer, an aluminum-based metal layer, a diffusion  
7 prevention layer, and a titanium layer;

8           wherein the diffusion prevention layer is a titanium nitride layer; and

9           wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1           5. (Previously Presented) The thin film transistor of claim 4, wherein the titanium  
2 nitride layer has a thickness of about 100 to 600Å.

1           6. (Original) The thin film transistor of claim 5, wherein the titanium nitride layer has  
2 a thickness of about 100 to 400Å.

1           7. (Original) The thin film transistor of claim 6, wherein the titanium nitride layer has  
2           a thickness of 200 to 400Å.

1           8. (Original) The thin film transistor of claim 7, wherein the titanium nitride layer has  
2           a thickness of about 300Å.

1           9. (Currently Amended) A thin film transistor, comprising a source electrode, a drain  
2           electrode, a gate electrode, and a semiconductor layer, wherein one of the source electrode,  
3           the drain electrode, and the gate electrode comprises ~~an aluminum-based metal layer, a~~  
4           ~~titanium layer, and a diffusion prevention layer interposed between the titanium and the~~  
5           ~~aluminum-based layers~~ an orderly stacked structure of a titanium layer, a diffusion  
6           prevention layer, an aluminum-based metal layer, a diffusion prevention layer, and a titanium  
7           layer, and wherein the aluminum-based metal layer is made of an aluminum alloy containing  
8           about 0.5 to 5 wt% of one element being selected from the group consisting of silicon,  
9           copper, neodymium, platinum, and nickel.

1           10. (Original) The thin film transistor of claim 9, wherein the aluminum-based metal  
2           layer is made of an aluminum-silicon alloy containing about 2 wt% of silicon.

Claims 11-13. (Canceled)

1           14. (Currently Amended) A flat panel display, comprising a plurality of sub-pixels  
2 driven by thin film transistors, each of the thin film transistors comprising a source  
3 electrode, a drain electrode, a gate electrode, and a semiconductor layer;

4           wherein at least one of the source electrode, the drain electrode, and the gate electrode  
5 comprises ~~an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer~~  
6 ~~interposed between the aluminum-based metal layer and the titanium layer~~ an orderly stacked  
7 structure of a titanium layer, a diffusion prevention layer, an aluminum-based metal layer,  
8 a diffusion prevention layer, and a titanium layer;

9           wherein the diffusion prevention layer is a titanium nitride layer; and

10          wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1           15. (Previously Presented) The flat panel display of claim 14, wherein the titanium  
2 nitride layer has a thickness of about 100 to 600Å.

1           16. (Original) The flat panel display of claim 15, wherein the titanium nitride layer  
2 has a thickness of about 100 to 400Å.

1           17. (Original) The flat panel display of claim 16, wherein the titanium nitride layer  
2 has a thickness of 200 to 400Å.

1           18. (Original) The flat panel display of claim 17, wherein the titanium nitride layer

has a thickness of about 300Å.

19. (Currently Amended) A flat panel display, comprising a plurality of sub-pixels driven by thin film transistors, each of the thin film transistors comprising a source electrode, a drain electrode, a gate electrode, and a semiconductor layer, wherein at least one of the source electrode, the drain electrode, and the gate electrode comprises ~~an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer interposed between the aluminum-based metal layer and the titanium layer~~ an orderly stacked structure of a titanium layer, a diffusion prevention layer, an aluminum-based metal layer, a diffusion prevention layer, and a titanium layer, and wherein the aluminum-based metal layer is made of an aluminum alloy containing about 0.5 to 5 wt% of one element being selected from the group consisting of silicon, copper, neodymium, platinum, and nickel.

20. (Original) The flat panel display of claim 19, wherein the aluminum-based metal layer is made of an aluminum-silicon alloy containing about 2 wt% of silicon.

21. (Currently Amended) A flat panel display, comprising:  
driving circuits disposed along edges of said display;  
a plurality of sub-pixels driven by thin film transistors; and  
conductive lines connecting the driving circuits disposed along edges of said display to each of said plurality of sub-pixels, wherein said conductive lines comprise ~~an~~

~~aluminum-based metal layer, a titanium layer, and a diffusion prevention layer interposed~~  
~~between the aluminum-based metal layer and the titanium layer~~ an orderly stacked structure  
of a titanium layer, a diffusion prevention layer, an aluminum-based metal layer, a diffusion  
prevention layer, and a titanium layer;

wherein the diffusion prevention layer is a titanium nitride layer; and

wherein said titanium nitride layer is 300 Å thick.

22. (Original) The flat panel display of claim 21, wherein the diffusion prevention layer and the titanium layer are orderly formed on opposite sides of the aluminum-based metal layer.

Claims 23-24. (Canceled)

25. (Previously Presented) The display of claim 22, said conductive lines being subjected to a heat treatment of 380°C.

26. (Currently Amended) A process for making a flat panel display, comprising:  
disposing driving circuits along edges of said display;  
arranging a plurality of sub-pixels driven by thin film transistors; and  
operatively connecting electrically conductive lines between the driving circuits disposed along edges of said display and each of said plurality of sub-pixels, wherein said conductive lines comprise ~~an aluminum-based metal layer, a titanium layer, and a diffusion~~

7 ~~prevention layer interposed between the aluminum-based metal layer and the titanium layer~~  
8 ~~an orderly stacked structure of a titanium layer, a diffusion prevention layer, an aluminum-~~  
9 ~~based metal layer, a diffusion prevention layer, and a titanium layer;~~

10 wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1 27. (Previously Presented) The process of claim 26, comprised of orderly forming the  
2 diffusion prevention layer and the titanium layer on opposite sides of the aluminum-based  
3 metal layer.

1 28. (Previously Presented) The process of claim 26, wherein the diffusion prevention  
2 layer is a titanium nitride layer.